

1-18. (Cancelled)

19. (Added) An active matrix display device, comprising:

an insulation substrate;

a thin film transistor formed on the insulation substrate, including a

semiconductor layer where source/drain regions are formed, gate electrode and source/drain electrodes respectively connected to the source/drain regions; an insulation film formed over the insulation substrate, having an opening portion; and a pixel electrode as a lower electrode, wherein the source/drain electrodes have a dual-layered structure of a transparent conductive layer and a metal layer, the metal layer being covered by the insulation film, wherein the pixel electrode extending from a portion of the transparent conductive layer forming any one of the source/drain electrodes and exposed through the opening portion of the insulation.

20. (Added) The active matrix display device according to claim 19, wherein the insulation layer is a passivation layer patterned to cover the metal layers of the source/drain electrodes.

21. (Added) The active matrix display device according to claim 19, wherein the insulation layer is a passivation layer reflowed to cover the metal layers of the source/drain electrodes.

22. (Added) The active matrix display according to claim 19, further comprising an organic EL layer formed on a portion of the pixel electrode exposed through the opening portion, wherein the organic EL layer is insulated from the metal layers of the source/drain electrodes.